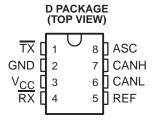
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- SN75LBC031 Meets Standard ISO/DIS 11898 (up to 500 k Baud)
- Driver Output Capability at 50 mA
- Wide Positive and Negative Input/output **Bus Voltage Range**
- **Bus Outputs Short-Circuit-Protected to Battery Voltage and Ground**
- **Thermal Shutdown**
- **Available in Q-Temp Automotive**
 - HighRel Automotive Applications
 - Configuration Control/Print Support
 - Qualification to Automotive Standards

description

The SN75LBC031 is a CAN transceiver used as an interface between a CAN controller and the physical bus for high speed applications of up to 500 kBaud. The device provides transmit capability to the differential bus and differential receive capability to the controller. The transmitter outputs (CANH and CANL), feature internal transition regulation to provide controlled symmetry resulting in low EMI emissions. Both



TERMINAL FUNCTIONS

TERMINAL	DESCRIPTION
TX	Transmitter input
GND	Ground
VCC	Supply voltage
RX	Receiver output
REF	Reference output
CANL	Low side bus output driver
CANH	High side bus output driver
ASC	Adjustable slope control

FUNCTION TABLE

TX	CANH	CANL	BUS STATE	RX
L	Н	L	Dominant	L
High or floating	Floating	Floating	Recessive	Н

transmitter outputs are fully protected against battery short circuits and electrical transients that can occur on the bus lines. In the event of excessive device power dissipation the output drivers are disabled by the thermal shutdown circuitry at a junction temperature of approximately 160°C. The inclusion of an internal pullup resistor on the transmitter input ensures a defined output during power up and protocol controller reset. For normal operation at 500 kBaud the ASC terminal is open or tied to GND. For slower speed operation at 125 kBaud the bus output transition times can be increased to reduce EMI by connecting the ASC terminal to V_{CC}. The receiver includes an integrated filter that suppresses the signal into pulses less than 30 ns wide.

The SN75LBC031 is characterized for operation from -40°C to 85°C. The SN65LBC031 is characterized for operation from -40°C to 125°C. The SN65LBC031Q is characterized for operation over the automotive temperature range of -40°C to 125°C.

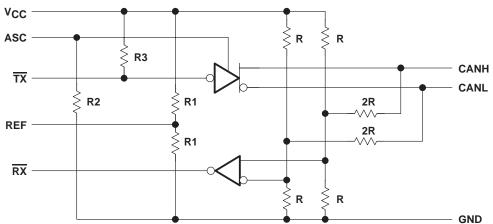


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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logic diagram



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Logic supply voltage, V _{CC} (see Note 1)	7 V
Bus terminal voltage	
Input current at TX and ASC terminal, I ₁	±10 mA
Input voltage at TX and ASC terminal, V _I	$\dots \dots 2 \times V_{CC}$
Operating free-air temperature range, T _A : SN65LBC031, SN65LBC031Q	40°C to125°C
SN75LBC031	40°C to 85°C
Operating juncation range, T _J	40°C to 150°C
Continuous total power dissipation at (or below) 25°C free-air temperature Se	ee Dissipation Rating Table
Storage temperature range, T _{stq}	65°C to 150°C
Case temperature for 10 sec T _C , D package	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values, except differential bus voltage, are measured with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	OPERATING FACTOR ABOVE T _C = 25°C	T _C = 125°C POWER RATING
D	725 mW	5.8 mW/°C	145 mW

DISSIPATION DERATING CURVE

vs

FREE-AIR TEMPERATURE

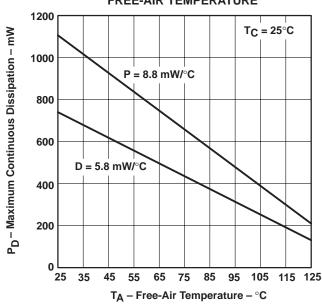


Figure 1

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recommended operating conditions

		MIN	NOM	MAX	UNIT	
Logic supply voltage, V _{CC}		4.5 5 5.5 \ -2 7 \ 2 VCC \ 0 0.8 \ -50 m -400 μ				
Voltage at any bus terminal (separately or common mode), V _I or V _{IC} (see Note 3)					V	
High-level input voltage, VIH	TX	2		VCC	V	
Low-level input voltage, V _{IL}	TX	0		0.8	V	
High level output current leve	Transmitter			-50	mA	
Low-level input voltage, V _{IL} High-level output current, I _{OH}	Receiver			-400	μΑ	
Low lovel output ourrent lov	Transmitter			50	A	
_ow-level input voltage, V _{IL}	Receiver			1	mA	
Operating free air temperature T.	SN75LBC031	-40		85	°C	
Operating free-air temperature, 1A	SN65LBC031, SN65LBC031Q	-40		125	-0	

NOTES: 2. All voltage values, except differential bus voltage, are measured with respect to the ground terminal.

3. For bus voltages from -5 V to -2 V and 7 V to 20 V the receiver output is stable.

SYMBOL DEFINITION

DATA SHEET PARAMETER	DEFINITION
VO(CANHR)	CANH bus output voltage (recessive state)
VO(CANLR)	CANL bus output voltage (recessive state)
VO(CANHD)	CANH bus output voltage (dominant state)
VO(CANLD)	CANL bus output voltage (dominant state)
VO(DIFFR)	Bus differential output voltage (recessive state)
V _{O(DIFFD)}	Bus differential output voltage (dominant state)
V _I (ASC)	Adjustable slope control input voltage

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VO(REF)	Reference source output voltage	I _{REF} = ±20 μA	0.45 V _{CC}		0.55 V _{CC}	V
R _{O(REF)}	Reference source output resistance		5		10	kΩ
ICC(REC)	Logic supply current, recessive state	See Figure 2, S1 closed		12	20	mA
ICC(DOM)	Logic supply current, dominant state	See Figure 2, ST Closed		55	80	IIIA

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transmitter electrical characteristics over recommended ranges of supply and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VO(CANHR) VO(CANLR)	Output voltage (recessive state)	See Figure 2, S1 open	2	0.5V _{CC}	3	V
V _{O(DIFFR)}	Differential output voltage (recessive state)		-500	0	50	mV
VO(CANHD)	Output voltage (dominant state)		2.75	3.5	4.5	
VO(CANLD)	Output voltage (dominant state)	See Figure 2, S1 closed	0.5	1.5	2.25	V
VO(DIFFD)	Differential output voltage (dominant state)		1.5	2	3	
	High-level input current (TX)	V _{IH} = 2.4 V		-100	-185	^
I _{IH} (TX)	righ-lever input current (1%)	VIH = VCC			±2	μΑ
l	High-level input current (ASC)	V _{IH} = 2.4 V		100	165	μΑ
IH(ASC)	righ-level input current (ASC)	V _{IH} = V _{CC}		200	340	μΑ
I _{IL(TX)}	Low-level input current (\overline{TX})	V _{IL} = 0.4 V		-180	-400	μΑ
IL(ASC)	Low-level input current (ASC)	V _{IL} = 0.4 V		15	25	μΑ
C _{I(TX)}	TX input capacitance			8		pF
I _{O(ssH)}	CANH short circuit output current	$V_{O(CANH)} = -2 V \text{ to } 20 V$		-95	-200	mA
I _{O(ssL)}	CANL short circuit output current	$V_{O(CANL)} = 20 \text{ V to } -2 \text{ V}$		140	250	mA

NOTE 2: All voltage values, except differential bus voltage, are measured with respect to the ground terminal.

transceiver dynamic characteristics over recommended operating free-air temperature range and V_{CC} = 5 V

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
	Loop time	See Figures 2 and 3, S1 closed,	VI(ASC) = 0 V or open circuit, S2 open			280	ns
^t (loop)	Loop time	See Figures 2 and 3, S1 closed,	V _I (ASC) = V _{CC} , S2 closed			400	ns
SR _(RD)	Differential-output slew rate	See Figures 2 and 4, S1 closed,	V _I (ASC) = 0 or open circuit, S2 open		35		V/μs
	(recessive to dominant)	See Figures 2 and 4, S1 closed,	VI(ASC) = VCC, S2 closed		10		V/μs
CD	Differential-output slew rate	See Figures 2 and 4, S1 closed,	V _I (ASC) = 0 or open circuit, S2 open		10		V/μs
SR _(DR)	(dominant to recessive)	See Figures 2 and 4, S1 closed,	VI(ASC) = VCC, S2 closed		10		V/μs
t _d (RD)	Differential output delay time	San Figure 2	S1 closed		55		ns
t _d (DR)	Differential-output delay time	See Figure 2,	ST Closed		160		ns
tpd(RECRD)	Receiver propagation delay	See Figures 2 and 5			90		ns
tpd(RECDR)	time	Gee i igules 2 aliu 5	See Figures 2 and 5		55		ns

NOTE 4: Receiver input pulse width should be >50 ns. Input pulses of <30 ns are suppressed.

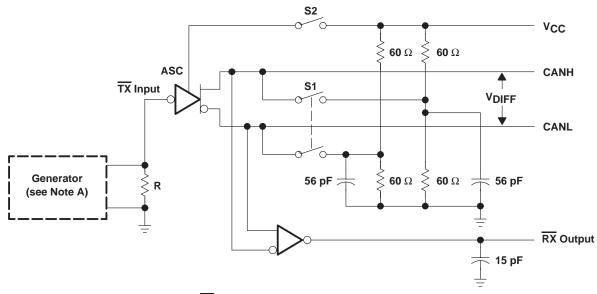
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receiver electrical characteristics over recommended ranges of common-mode input voltage, supply voltage, and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIT(REC)	Differential input threshold voltage for recessive state	V _{IC} = -2 V to 7 V			500	mV
VIT(DOM)	Differential input threshold voltage for dominant state	VIC = -2 V 10 7 V	900			IIIV
V _{hys}	Recessive-dominant input hysteresis		100	180		mV
VOH(RX)	High-level output voltage	$V_{O(DIFF)} = 500 \text{ mV},$ $I_{OH} = -400 \mu\text{A}$	V _{CC} -0.5 V		VCC	V
V _{OL(RX)}	Low-level output voltage	$V_{O(DIFF)} = 900 \text{ mV},$ $I_{OL} = 1 \text{ mA}$	0		0.5	V
rI(REC)	CANH and CANL input resistance in recessive state	dc, no load	5		50	kΩ
rI(DIFF)	Differential CANH and CANL input resistance in recessive state	dc, no load	10		100	kΩ
Ci	CANH and CANL input capacitance			20		pF
C _{i(DHL)}	Differential CANH and CANL input capacitance			10		pF

NOTE 2: All voltage values, except differential bus voltage, are measured with respect to the ground terminal.

PARAMETER MEASUREMENT INFORMATION



NOTE A: The input pulse is supplied to \overline{TX} by a generator having a t_f and $t_f = 5$ ns.

Figure 2. Test Circuit

PARAMETER MEASUREMENT INFORMATION

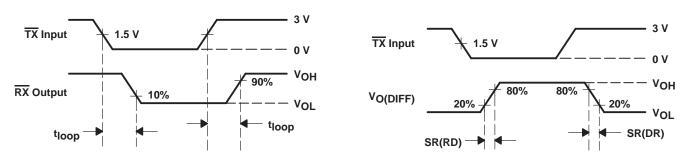
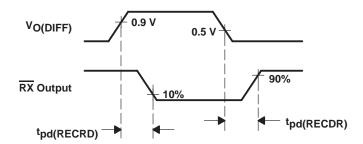


Figure 3. Loop Time

Figure 4. Slew Rate

NOTE A: The input pulse is supplied to \overline{TX} by a generator having a t_{Γ} and $t_{f} = 5$ ns.



NOTE A: The input pulse is supplied as V_{DIFF} using CANH and CANL respectively by a generator having a t_r and $t_f = 5$ ns.

Figure 5. Receiver Delay Times

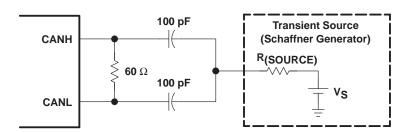


Figure 6. Transient Stress Capability Test Circuit

PARAMETER MEASUREMENT INFORMATION

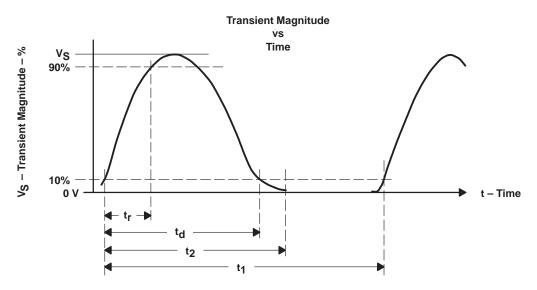


Figure 7. Transient Stress Capability Waveform

Table 1. Test Circuit Results According to DIN 40839

TEST PULSE	TRANSIENT MAGNITUDE VS	SOURCE IMPEDANCE RSOURCE	PULSE WIDTH t _d (see Note 5)	PULSE RISE TIME, t _r (see Note 6)	PULSE TIME, t ₂ (see Figure 7)	REPETITION PERIOD, t ₁ (see Figure 7)	NUMBER OF PULSES
1	–100 V	10 Ω	2 ms	1 μs	200 ms	5 s	5000
2	100 V	10 Ω	50 μs	1 μs	200 ms	5 s	5000
3a	−150 V	50 Ω	0.1 μs	5 ns	100 μs	100 μs	See Note 7
3b	100 V	50 Ω	0.1 μs	5 ns	100 μs	100 μs	See Note 7
5	60 V	1 Ω	400 ms	5 ms	_	_	1

NOTES: 5. Measured from 10% on rising edge to 10% on falling edge

- 6. Measured from 10% to 90% of pulse
- 7. Pulse package for a period of 3600 s, 10 ms pulse time, 90 ms stop time

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APPLICATION INFORMATION 5 V 💳 100 nF 3 120 Ω \lesssim 10 k Ω 10 kΩ § 8 **VCC VCC** 8 **ASC** TL7705B **CANH** 7 SENSE SN75LBC031 RESIN RESET GND CANL REF **GND** c_{in} TX REF RX 120 Ω 5 $\textbf{0.1}~\mu\textbf{F}$ 4 **CAN Microcontroller**

Figure 8. Typical SN75LBC031 Application

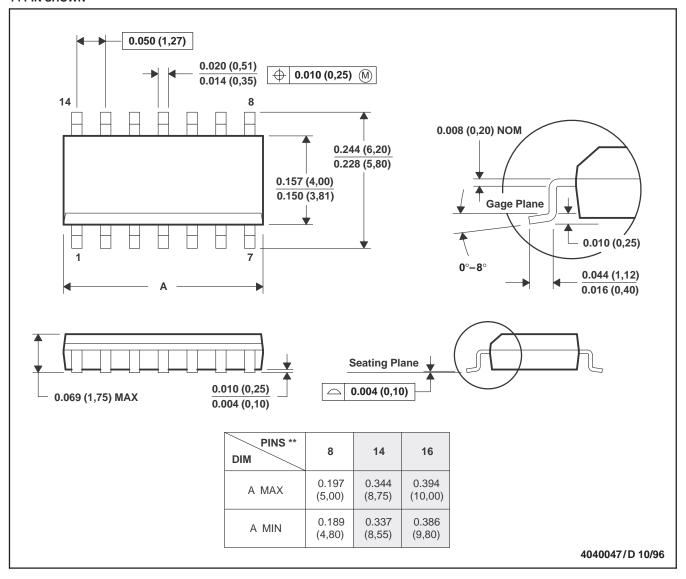
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MECHANICAL DATA

D (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-012





11-Jan-2021

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN65LBC031D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-220C-UNLIM	-40 to 85	6LB031	Samples
SN65LBC031DG4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB031	Samples
SN65LBC031DRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		6LB031	Samples
SN65LBC031QD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	6LB031Q	Samples
SN65LBC031QDG4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	6LB031Q	Samples
SN65LBC031QDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB031Q	Samples
SN65LBC031QDRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LB031Q	Samples
SN75LBC031D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	7LB031	Samples
SN75LBC031DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	7LB031	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

11-Jan-2021

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

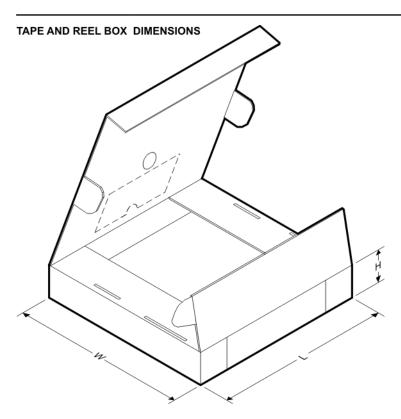
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LBC031QDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LBC031QDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75LBC031DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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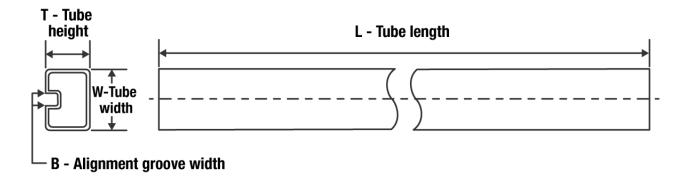
*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LBC031QDR	SOIC	D	8	2500	350.0	350.0	43.0
SN65LBC031QDRG4	SOIC	D	8	2500	350.0	350.0	43.0
SN75LBC031DR	SOIC	D	8	2500	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65LBC031D	D	SOIC	8	75	505.46	6.76	3810	4
SN65LBC031DG4	D	SOIC	8	75	505.46	6.76	3810	4
SN65LBC031QD	D	SOIC	8	75	505.46	6.76	3810	4
SN65LBC031QDG4	D	SOIC	8	75	505.46	6.76	3810	4
SN75LBC031D	D	SOIC	8	75	505.46	6.76	3810	4



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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